

Power management (dual transistors)

EMF32 / UMF32N

DTA143T and 2SK3019 are housed independently in a EMT6 package.

Application

Power management circuit

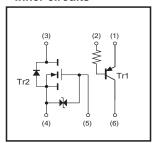
● Features

- 1) Power switching circuit in a single package.
- 2) Mounting cost and area can be cut in half.

●Structure

Silicon epitaxial planar transistor

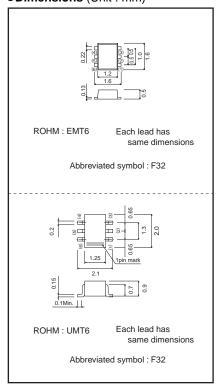
•Inner circuits



Packaging specifications

Туре	EMF32	UMF32N
Package	EMT6	UMT6
Marking	F32	F32
Code	T2R	TR
Basic ordering unit (pieces)	8000	3000

●Dimensions (Unit : mm)



EMF32 / UMF32N Data Sheet

●Absolute maximum ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit
Collector-base voltage	Vсво	-50	V
Collector-emitter voltage	Vceo	-50	V
Emitter-base voltage	Vево	-5	V
Collector current	Ic	-100	mA
Power dissipation	Pc	150(TOTAL)	mW *1
Junction temperature	Tj	150	°C
Range of storage temperature	Tstg	-55 to +150	°C

^{*1 120}mW per element must not be exceeded. Each terminal mounted on a recommended land.

Tr2

Parameter		Symbol	Limits	Unit
Drain-source voltage		VDSS	30	V
Gate-source voltage		Vgss	±20	V
Drain current	Continuous	ΙD	100	mA
	Pulsed	IDP	200	mA *1
Reverse drain current	Continuous	Idr	100	mA
	Pulsed	IDRP	200	mA *1
Total power dissipation		P□	150(TOTAL)	mW *2
Channel temperature		Tch	150	°C
Range of storage temperature		Tstg	-55 to +150	°C

●Electrical characteristics (Ta=25°C) Tr1

** *						
Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Collector-base breakdown voltage	ВУсво	-50	-	-	V	Ic= -50μA
Collector-emitter breakdown voltage	BVceo	-50	_	-	V	Ic=-1mA
Emitter-base breakdown voltage	ВУЕВО	-5	-	-	V	I _E = -50μA
Collector cutoff current	Ісво	-	-	-0.5	μΑ	Vcb= -50V
Emitter cutoff current	ІЕВО	_	_	-0.5	μΑ	V _{EB} = -4V
Collector-emitter saturation voltage	VCE(sat)	_	_	-0.3	V	Ic/I _B = -5mA/ -0.25mA
DC current transfer ratio	hfe	100	250	600	_	Ic=-1mA, Vc==-5V
Input resistance	R ₁	3.29	4.7	6.11	kΩ	_
Transition frequency	f⊤	-	250	-	MHz	Vce= -10V, Ie=5mA, f=100MHz

^{*} Transition frequency of the device

Tr2

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions	
Gate-source leakage	Igss	_	_	±1	μΑ	Vgs=±20V, Vps=0V	
Drain-source breakdown voltage	V(BR)DSS	30	_	_	V	In=10μA, Vgs=0V	
Zero gate voltage drain current	IDSS	_	_	1.0	μΑ	V _{DS} =30V, V _{GS} =0V	
Gate-threshold voltage	VGS(th)	0.8	_	1.5	V	V _{DS} =3V, I _D =100μA	
Static drain-source on-state resistance	RDS(on)	_	5	8	Ω	In=10mA, Vgs=4V	
		_	7	13	Ω	ID=1mA, VGS=2.5V	
Forward transfer admittance	Yfs	20	_	_	ms	V _{DS} =3V, I _D =10mA	
Input capacitance	Ciss	_	13	_	pF		
Output capacitance	Coss	_	9	_	pF	V _{DS} =5V, V _{GS} =0V, f=1MHz	
Reverce transfer capacitance	Crss	_	4	_	pF	1	
Turn-on delay time	td(on)	_	15	_	ns		
Rise time	tr	_	35	_	ns	ID=10mA, VDD ≒5V,	
Turn-off delay time	td(off)	_	80	_	ns	Vgs=5V, RL=500 Ω , Rgs=10 Ω	
Fall time	tr	_	80	_	ns	1100-1022	

^{*1} PW:10ms Duty cycle≤50%
*2 120mW per element must not be exceeded. Each terminal mounted on a recommended land.

EMF32 / UMF32N Data Sheet

•Electrical characteristic curves

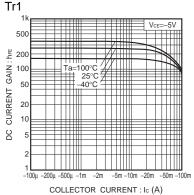


Fig.1 DC current gain vs. collector

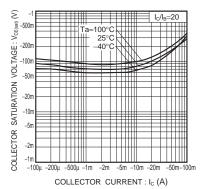


Fig.2 Collector-emitter saturation voltage vs. collector current

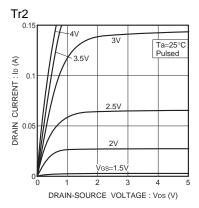


Fig.3 Typical output characteristics

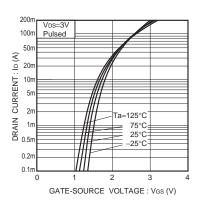


Fig.4 Typical transfer characteristics

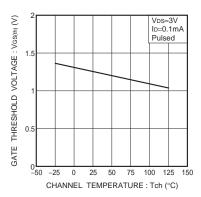


Fig.5 Gate threshold voltage vs. channel temperature

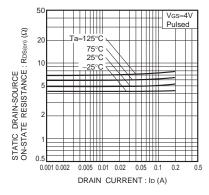


Fig.6 Static drain-source on-state resistance vs. drain current (I)

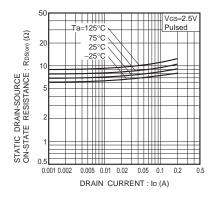


Fig.7 Static drain-source on-state resistance vs. drain current (II)

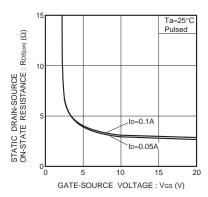


Fig.8 Static drain-source on-state resistance vs. gate-source voltage

EMF32 / UMF32N Data Sheet

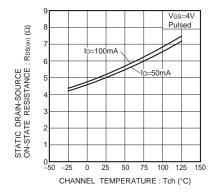


Fig.9 Static drain-source on-state resistance vs. channel temperature

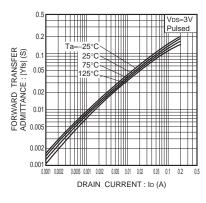


Fig.10 Forward transfer admittance vs. drain current

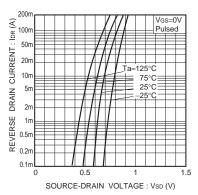


Fig.11 Reverse drain current vs. source-drain voltage (I)

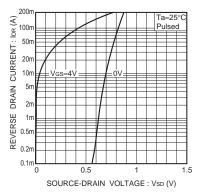


Fig.12 Reverse drain current vs. source-drain voltage (II)

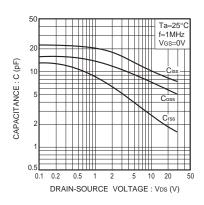


Fig.13 Typical capacitance vs. drain-source voltage

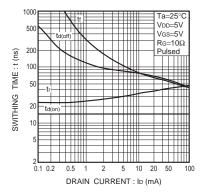


Fig.14 Switching characteristics

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